Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = 25°C
30V	12mΩ @ V_{GS} = 10V	10A
	16mΩ @ V_{GS} = 4.5V	8.5A

Features and Benefits

- 0.6mm profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm^2
- Low Gate Threshold Voltage
- Low On-Resistance
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMN3016LFDFQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

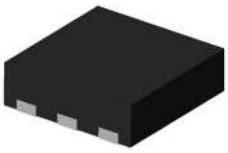
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and ideal for use in:

- Battery Management Applications
- Power Management Functions
- DC-DC Converters

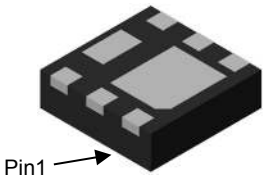
Mechanical Data

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.0065 grams (Approximate)

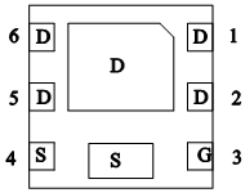
U-DFN2020-6 (Type F)



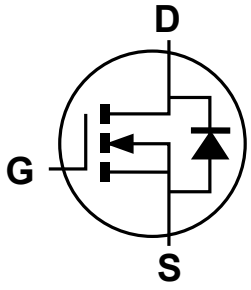
Top View



Bottom View



Pinout
Bottom View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3016LFDFQ-7	U-DFN2020-6 (Type F)	3000/Tape & Reel
DMN3016LFDFQ-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3).compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Site 1

NZ = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: I = 2021)
M = Month (ex: 9 = September)

Date Code Key

Year	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	I	J	K	L	M	N	O	P	R	S	T	U

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Site 2

NZ = Product Type Marking Code
YWX = Date Code Marking
Y = Year (ex: 1 = 2021)
W = Week (ex: a = Week 27; z Represents Week 52 and 53)
X = Internal Code (ex: U = Monday)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026
Code	9	0	1	2	3	4	5	6

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Y	Z

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	10 8	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	12 9	A
Maximum Continuous Body Diode Forward Current (Note 5)			I_S	2.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	50	A
Avalanche Current (Note 7) L = 0.1mH			I_{AR}	22	A
Avalanche Energy (Note 7) L = 0.1mH			E_{AR}	24	mJ

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.73	W
	T_A = +70°C		0.47	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	174	°C/W
	t<10s		121	
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	2.02	W
	T_A = +70°C		1.30	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	66	°C/W
	t<10s		42	
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{\theta JC}$	11.6	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.4	—	2.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	8	12	mΩ	V_{GS} = 10V, I_D = 11A
		—	12	16		V_{GS} = 4.5V, I_D = 9A
Diode Forward Voltage	V_{SD}	—	0.70	1.0	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	1415	—	pF	V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	119	—		
Reverse Transfer Capacitance	C_{rss}	—	82	—		
Gate Resistance	R_g	—	2.6	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	11.3	—	nC	V_{DS} = 15V, I_D = 12A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	25.1	—		
Gate-Source Charge	Q_{gs}	—	3.5	—		
Gate-Drain Charge	Q_{gd}	—	3.6	—		
Turn-On Delay Time	$t_{D(ON)}$	—	4.8	—	ns	V_{DD} = 15V, V_{GS} = 10V, R_L = 1.25Ω, R_g = 3Ω
Turn-On Rise Time	t_R	—	16.5	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	26.1	—		
Turn-Off Fall Time	t_F	—	5.6	—		
Reverse Recovery Time	t_{RR}	—	12.3	—	ns	I_F = 12A, di/dt = 500A/µs
Reverse Recovery Charge	Q_{RR}	—	10.4	—	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

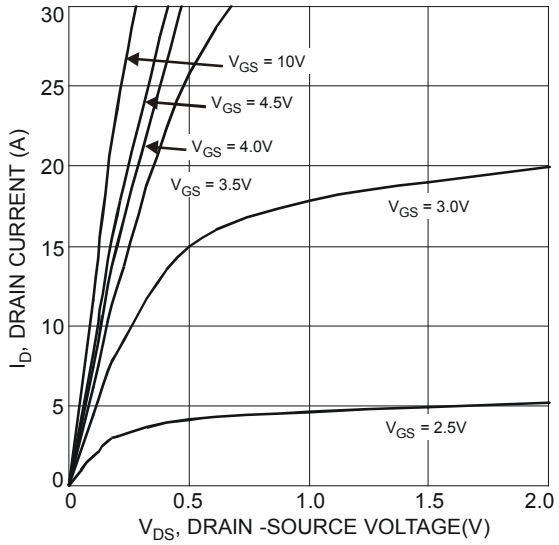


Fig. 1 Typical Output Characteristics

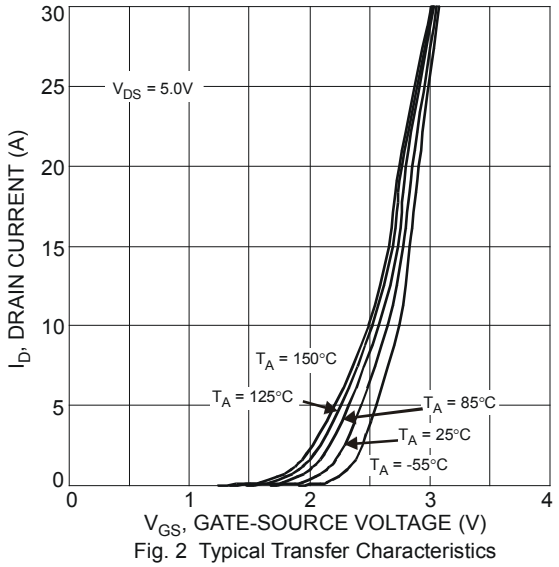


Fig. 2 Typical Transfer Characteristics

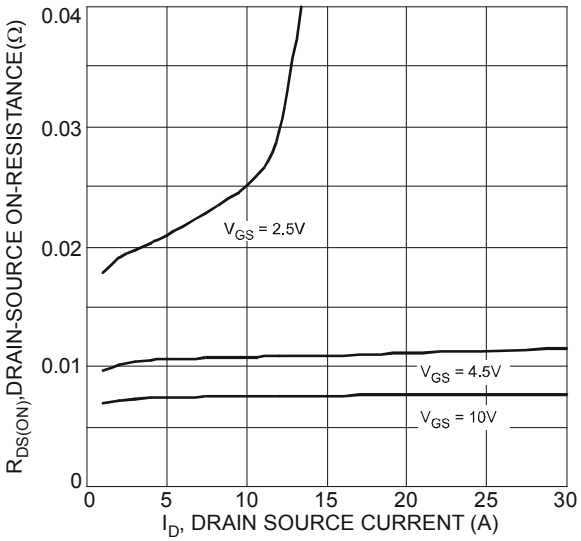


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

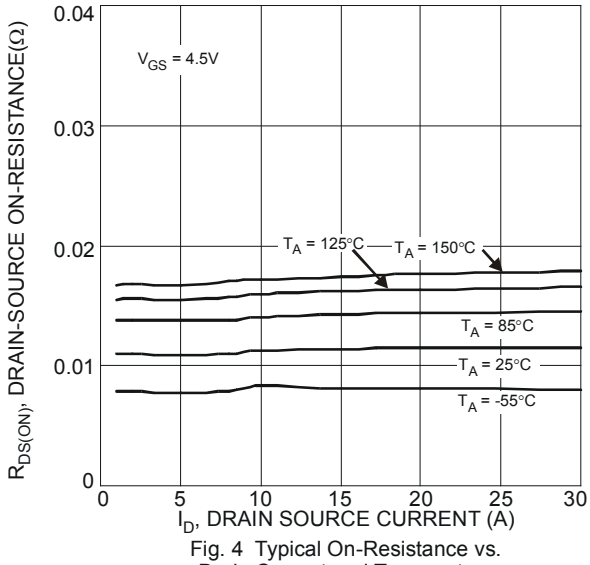


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

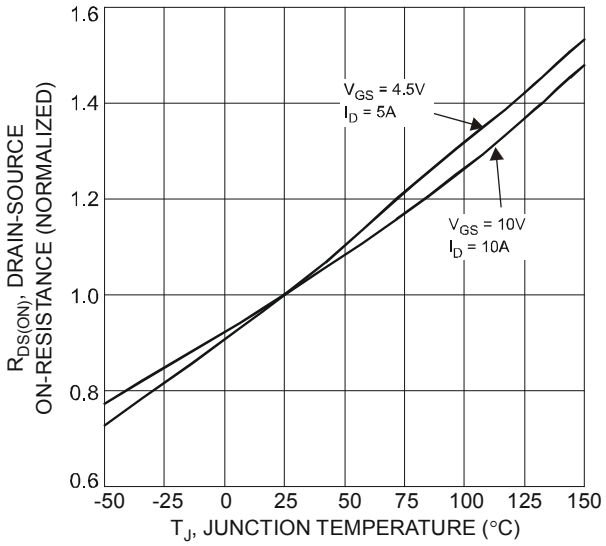


Fig. 5 On-Resistance Variation with Temperature

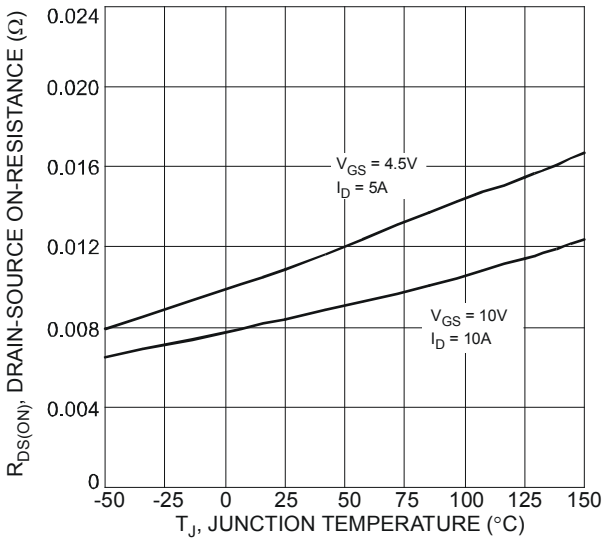


Fig. 6 On-Resistance Variation with Temperature

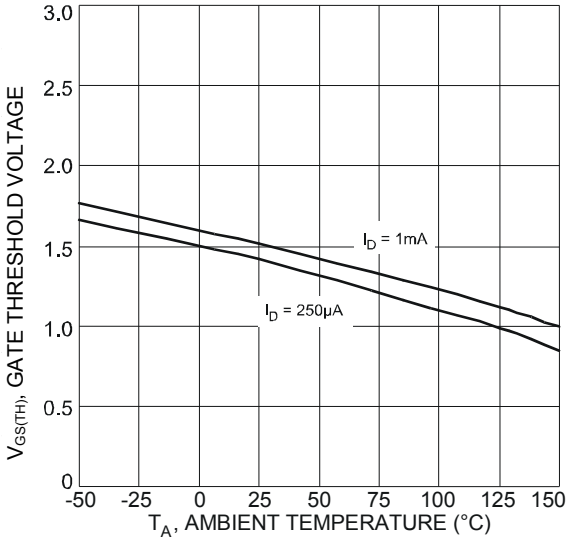


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

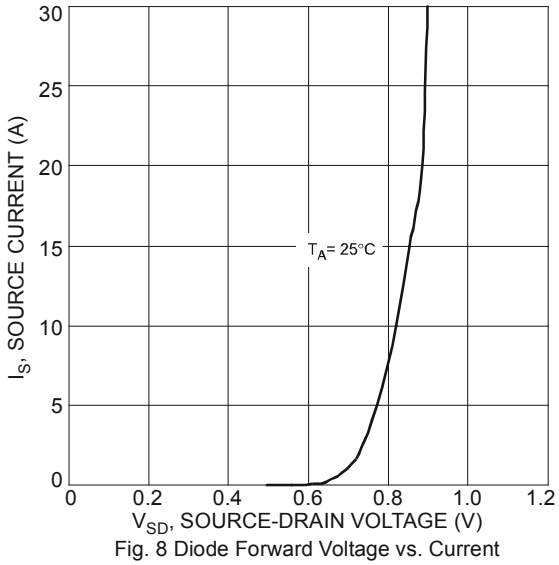


Fig. 8 Diode Forward Voltage vs. Current

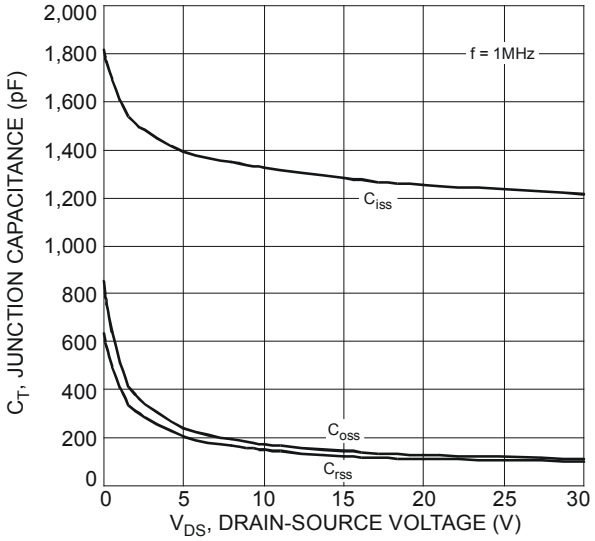


Fig. 9 Typical Junction Capacitance

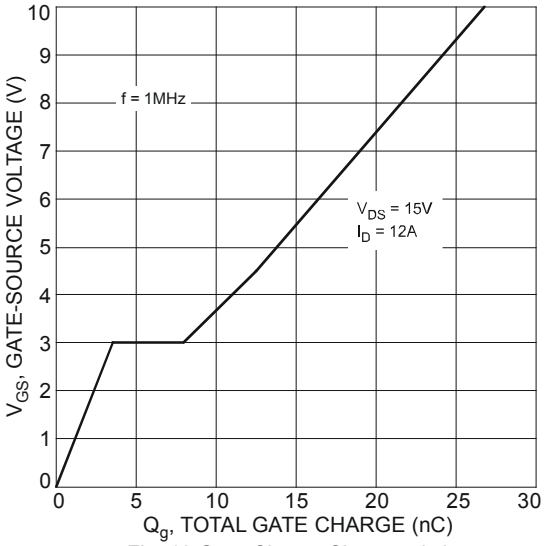


Fig. 10 Gate-Charge Characteristics

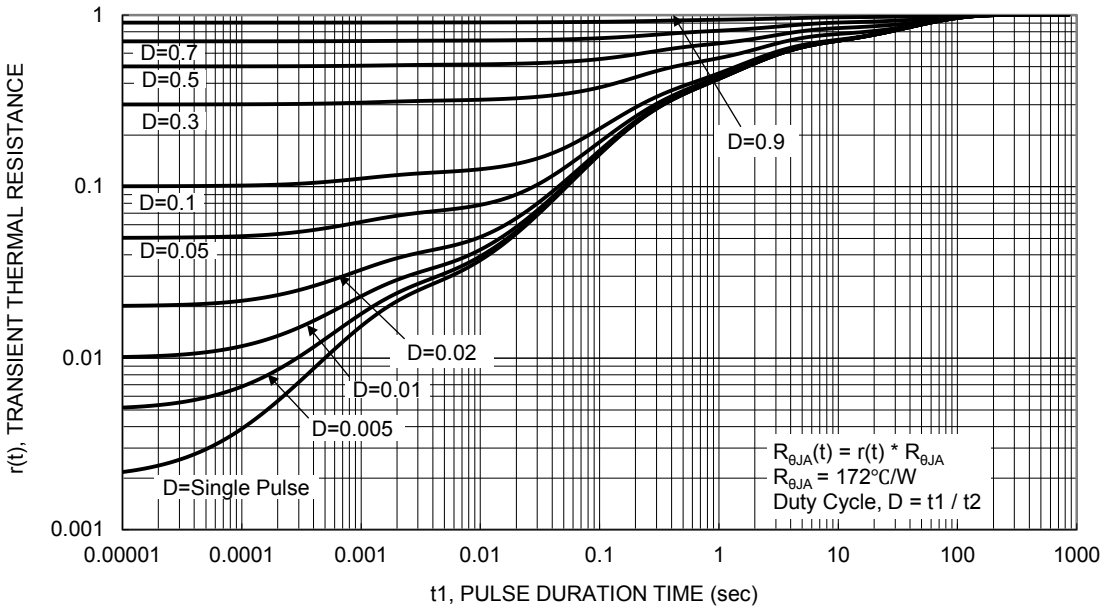
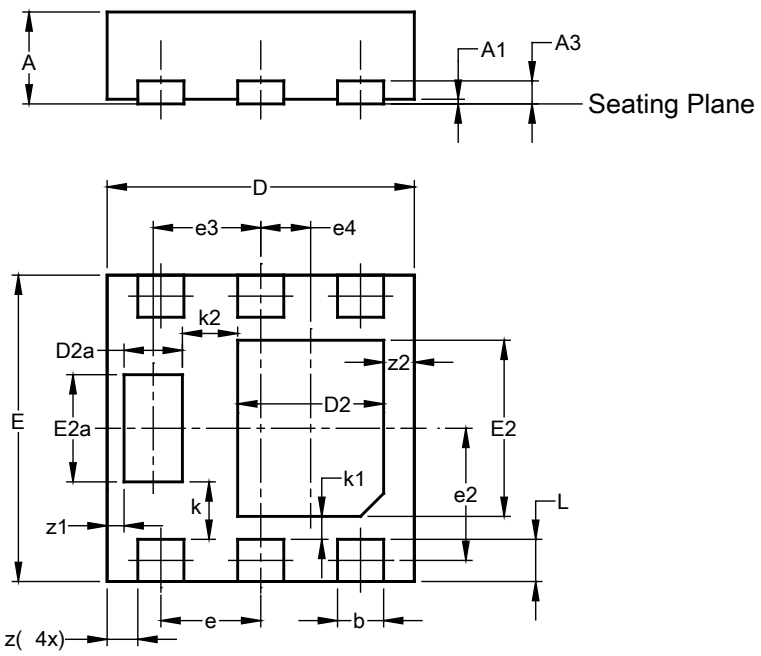


Figure 11. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

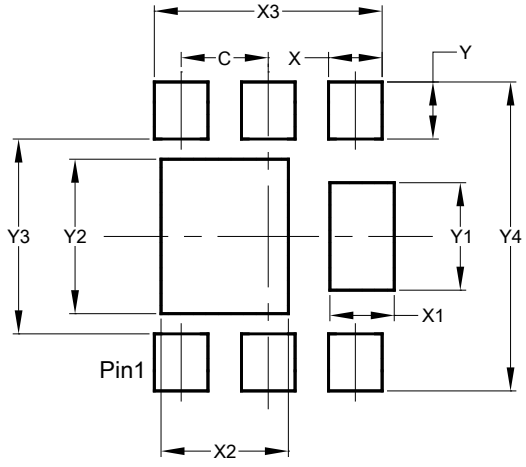


U-DFN2020-6 (Type F)			
Dim	**Min**	**Max**	**Typ**
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D2a	0.33	0.43	0.38
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E2a	0.65	0.75	0.70
e	0.65 BSC		
e2	0.863 BSC		
e3	0.70 BSC		
e4	0.325 BSC		
k	0.37 BSC		
k1	0.15 BSC		
k2	0.36 BSC		
L	0.225	0.325	0.275
z	0.20 BSC		
z1	0.110 BSC		
z2	0.20 BSC		
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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